Form PTO-1449	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. DOCKET NO.	SERIAL NO.
		JG00009	
		El-Zein et al.	
		FILING DATE	GROUP
		July 24, 2000	

JC864 U.S. PTO 09/624691 07/24/00

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER							ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
	AA	5	2	7	0	2	9	8	12/14-93	Ramesh	505	1	8/4/92
	AB	5	4	1	8	3	8	9	5/23/95	Watanabe	257	295	11/9/93
	AC	5	2	4	8	5	6	4	9/28/93	Ramesh	428	688	12/9/92
	AD	5	1	5	5	6	5	8	10/13/92	Inam et al.	361	321	3/5/92
	AE	6	0	5	5	1	7	9	4/25/00	Koganei et al.	365	158	5/17/99
	AF	5	3	2	6	7	2	1	7/5/94	Summerfelt	437	131	5/1/92
	AG	5	3	1	0	7	0	7	5/10/94	Oishi et al.	501	126	9/28/92
	AH	4	9	9	9	8	4	2	3/12/91	Huang et al.	372	45	3/1/89
	AI	5	8	7	4	8	6	0	2/23/99	Brunel et al.	330	285	12/4/96
	AJ	6	0	0	2	3	7	5	12/14/99	Corman et al.	343	853	9/2/97
	AK	4	8	8	2	3	0	0	11/21/89	Inoue et al.	437	236	10/6/88
	AL	5	6	7	4	3	6	6	10/7/97	Hayashi et al.	204	298.09	6/7/95
	AM	5	7	3	1	2	2	0	3/24/98	Tsu et al.	437	60	6/7/95
	AN	5	8	2	8	0	8	0	10/27/98	Yano et al.	257	43	8/17/95
	AO	5	8	0	1	1	0	5	9/1/98	Yano et al.	438	785	6/14/96

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AP	"Optimizing GMR Spin Valves: The Outlook for Improved Properties", W. F. Englhoff et al., 1998 Int'l NonVolatile Memory Technology Conference, pp. 34-37.
	AQ	"Processing and Performance of Piezoelectric Films", Y. Wang et al. , Univ. of MD, Wilcoxon Research Co., and Motorola Labs.
	AR	"Nonlinear acoustoelectric interactions in GaAs/$LiNbO_3$ structures", M. Rotter et al., 1999 American Institute of Physics, pp. 965-967.
	AS	"Surface acoustic wave propagation on lead zirconate titanate thin films", K. Sreenivas et al., App. Phys. Lett. 52(9), 29 February 1988, pp. 709-711.
	AT	"Single Chip fused hybrids for acousto-electric and acousto-optic applications", M. Rotter et al., 1997 American Institute of Physics, pp. 2097-2099.
	AU	"Surface Acoustic Wave Propagation in PZT/YBCO/$SrTiO_3$ and PbTi O_3/YBCO/$SrTiO_3$ Epitaxial Heterostructures", Dept. of Physics & Astrophysics, Univ. of Delhi, pp. 275-283.
	AV	"Ferroelectric Field Effect Transisitor Based on Epitaxial Perovskite Heterostructures", S. Mathews et al., American Association for the Advancement of Science, 1997, pp.238-240.

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JC854 U.S. PTO 09/624691 07/24/00

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	GRANT DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES	TRANSLATION NO
	AK							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AL	"Formation of Si Epi./Mg0-Al_20_3 Epi./$Si0_3$/Si and Its Epitaxial Film Quality," Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.
	AM	"An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF_2 and Silicon," T. Asano et al., Graduate School of Science and Engineering, Tokyo Institute of Technology, pp. 143-151.
	AN	"Reaction and Regrowth Control of $Ce0_2$ on Si(111) Surface for the Silicon-On-Insulator Structure," T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.
	AO	"Epitaxial Growth of $Ce0_2$(100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," J.F. Kang et al., Solid State Communications, Vol. 108, No. 4, pp. 225-227.
	AP	"Vertical-Cavity Surface-Emitting Lasers Come of Age," Robert A. Morgan et al., SPIE, Vol. 2683, pp. 18-29.
	AQ	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone(Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.

EXAMINER	DATE CONSIDERED
	6/02

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